BogusÅ‚awa Adamowicz

List of Publications by Year
in descending order

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39 papers	894 citations	567281 15 h-index	454955 30 g-index
39 all docs	39 docs citations	39 times ranked	1105 citing authors

#	Article	IF	Citations
1	XPS study of the L-CVD deposited SnO2 thin films exposed to oxygen and hydrogen. Thin Solid Films, 2001, 391, 198-203.	1.8	216
2	Effects of interface states and temperature on the C-V behavior of metal/insulator/AlGaN/GaN heterostructure capacitors. Journal of Applied Physics, 2008, 103, .	2.5	172
3	Surface passivation of IIIâ€“V semiconductors for future CMOS devicesâ€”Past research, present status and key issues for future. Applied Surface Science, 2010, 256, 5698-5707.	6.1	63
4	The comparative XPS and PYS studies of SnO2 thin films prepared by L-CVD technique and exposed to oxygen and hydrogen. Sensors and Actuators B: Chemical, 2000, 70, 177-181.	7.8	57
5	On the origin of interface states at oxide/III-nitride heterojunction interfaces. Journal of Applied Physics, 2016, 120, .	2.5	41
6	Computer Analysis of Surface Recombination Process at Si and Compound Semiconductor Surfaces and Behavior of Surface Recombination Velocity. Japanese Journal of Applied Physics, 1998, 37, 1631-1637.	1.5	36
7	Simulations of Capacitanceâ€“Voltageâ€“Temperature Behavior of Metal/Insulator/AlGaN and Metal/Insulator/AlGaN/GaN Structures. Japanese Journal of Applied Physics, 2009, 48, 04C092.	1.5	32
8	Determination of the deep donor-like interface state density distribution in metal/Al2O3/n-GaN structures from the photocapacitanceâ€“light intensity measurement. Applied Physics Letters, 2012, 101, .	3.3	24
9	Response to oxygen and chemical properties of SnO2 thin-film gas sensors. Vacuum, 2008, 82, 966-970.	3.5	22
10	Characterization of capture cross sections of interface states in dielectric/III-nitride heterojunction structures. Journal of Applied Physics, 2016, 119, .	2.5	21
11	Dynamics and control of recombination process at semiconductor surfaces, interfaces and nano-structures. Solar Energy, 2006, 80, 629-644.	6.1	20
12	Near-band gap transitions in the surface photovoltage spectra for GaAs, GaP and Si surfaces. Surface Science, 1991, 247, 94-99.	1.9	19
13	Origin of positive fixed charge at insulator/AlGaN interfaces and its control by AlGaN composition. Applied Physics Letters, 2017, 110, 243505.	3.3	19
14	Surface electronic properties of sulfur-treated GaAs determined by surface photovoltage measurement and its computer simulation. Surface Science, 2009, 603, 498-502.	1.9	18
15	Disorder induced gap states as a cause of threshold voltage instabilities in Al2O3/AlGaN/GaN metal-oxide-semiconductor high-electron-mobility transistors. Journal of Applied Physics, 2017, 122, .	2.5	16
16	Surface photovoltage and Auger electron spectromicroscopy studies of HfO2/SiO2/4H-SiC and HfO2/Al2O3/4H-SiC structures. Applied Surface Science, 2012, 258, 8354-8359.	6.1	14
17	Computer analysis of an influence of oxygen vacancies on the electronic properties of the SnO2surface and near-surface region. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 2241-2246.	1.8	12
18	A novel IIIâ€“V semiconductor material for NO2 detection and monitoring. Sensors and Actuators A: Physical, 2008, 142, 237-241.	4.1	11

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19	XPS, electric and photoluminescence-based analysis of the GaAs (100) nitridation. Applied Surface Science, 2006, 252, 7890-7894.	6.1	10
20	Investigation of electron processes at the p and n type Si(111) real surface by the surface photovoltage method. Surface Science, 1990, 231, 1-8.	1.9	9
21	Computer analysis of photoluminescence efficiency at InP surface with U-shaped surface state continuum. Vacuum, 2001, 63, 223-227.	3.5	9
22	Photoluminescence characterization of air exposed AlGaAs surface and passivated ex situ by ultrathin silicon interface control layer. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 261-266.	2.7	8
23	Analysis of photoluminescence efficiency and surface recombination velocity of MBE-grown AlGaAs layers. Thin Solid Films, 2000, 367, 180-183.	1.8	7
24	Capacitance-voltage and photoluminescence study of high-kâˆ•GaAs interfaces controlled by Si interface control layer. Journal of Vacuum Science & Technology B, 2009, 27, 2028.	1.3	6
25	Rigorous analysis of photoluminescence efficiency for characterisation of electronic properties of InP(100) surfaces. Vacuum, 2002, 67, 3-10.	3.5	5
26	Surface state density distribution at vacuum-annealed InP(100) surface as derived from the rigorous analysis of photoluminescence efficiency. Applied Surface Science, 2008, 254, 8046-8049.	6.1	5
27	Computer simulations of the surface photovoltage on Si and GaAs surfaces with U-shaped surface state continuum. Vacuum, 1999, 54, 173-177.	3.5	4
28	Computer analysis of photon-induced non-equilibrium phenomena at Si and AlGaAs surfaces. Vacuum, 2000, 57, 111-120.	3.5	4
29	The contribution of surface effects to the surface photovoltage dependence on temperature for the real Si(111) surface. Surface Science, 1988, 200, 172-178.	1.9	3
30	Electronic properties of AlxGa1âˆ’xAs surface passivated by ultrathin silicon interface control layer. Applied Surface Science, 1999, 141, 326-332.	6.1	3
31	Rigorous analysis of the electronic properties of InP interfaces for gas sensing. Thin Solid Films, 2003, 436, 101-106.	1.8	3
32	Impact of Interface States and Bulk Carrier Lifetime on Photocapacitance of Metal/Insulator/GaN Structure for Ultraviolet Light Detection. Japanese Journal of Applied Physics, 2011, 50, 04DF08.	1.5	2
33	Role of interface states and depletion layer in NO2 sensing mechanism of n-InP epitaxial layers. Sensors and Actuators A: Physical, 2012, 181, 43-50.	4.1	2
34	Dependence of silicon surface electronic parameters on surface Fermi level position. Vacuum, 1994, 45, 167-170.	3.5	1
35	Electronic Properties of the Clean and Oxygen Exposed GaAs(lOO) Surface. Studies in Surface Science and Catalysis, 1988, 40, 229-231.	1.5	0
36	Inverse photoemission and Kelvin probe studies of the Au/GaP(110) interface. Vacuum, 1995, 46, 509-512.	3.5	0

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37	Room temperature photoluminescence studies of nitrided InP(100) surfaces. Materials Science and Engineering C, 2006, 26, 378-382.	7.3	0
38	The influence of interface states and bulk carrier lifetime on the minority carrier behavior in an illuminated metal/insulator/GaN structure. Solid State Communications, 2011, 151, 830-833.	1.9	0
39	A novel method for the determination of the full energetic distribution of interface state density in metal/insulator/GaN structures from capacitance - voltage and photocapacitance - light intensity measurements. , 2013, , .		0